

## 1083 nm Laser Diode

### Description

The IDP1083DBR Series of high-power edge-emitting lasers are based on Idealphotonics's advanced single-frequency laser technology. It provides a diffraction limited, single lateral and longitudinal mode beam. Facets are passivated for high-power reliability. Applications for the 1083 nm laser diode include fiber amplifier seeding, spectroscopy, difference frequency generation, and low power DPSS replacement. The Spectroscopy Series 1083 nm laser diode is certified to be resonant with the metastable helium line.

### Feature

- WAvaliable in several package styles
- Pulsed operation for spectral stability at short pulse lengths
- High power for CW applications
- High Slope Efficiency

### Technology

- DBR Single-Frequency Laser Chip
- AlGaAs QW Active Layer
- Epi designed for high reliability

### Specification

#### Absolute Maximum Rating

Parameter	Symbol	Unit	Min	Max
Storage Temperature	T <sub>STG</sub>	°C	0	80
Operating Temperature	T <sub>OP</sub>	°C	5.0	70
CW Laser Forward Current, T=T <sub>op</sub>	I <sub>F</sub>	mA	-	300**
Pulsed Laser Forward Current, T=25°C, PW=300 ns, DC=10%	I <sub>F</sub>	A	-	1.0
Laser Reverse Voltage	V <sub>R</sub>	V	-	2.0
Photodiode Forward Current 1/ 2/	I <sub>P</sub>	mA	-	5.0
Photodiode Reverse Voltage 1/ 2/	V <sub>R</sub>	V	-	20.0
Photodiode Dark Current, V <sub>R</sub> =10V, LD I <sub>F</sub> =0, 1/ 2/	I <sub>D</sub>	nA	-	50
TEC Current 1/ 2/	I <sub>TEC</sub>	A	-2.5	2.5



TEC Voltage <u>1/ 2/</u>	V <sub>TEC</sub>	V	-6.0	6.0
Thermistor Current <u>1/ 2/</u>	I <sub>THRM</sub>	mA	-	1.0
Thermistor Voltage <u>1/ 2/</u>	V <sub>THRM</sub>	V	-	10
ESD (HBM)	-	V	-	500
External Back Reflection	-	dB	-	-14
Lead Soldering Temperature, 10 sec. Max., <u>1/ 2/</u>	-	°C	-	260
Fiber Pull Force <u>1/</u>	-	N	-	5.0
Fiber Bend Radius <u>1/</u>	-	mm	-	35

1/ Butterfly package 2/ TO8 package\*\*Do not exceed drive current or operating power of supplied LIV

CW Characteristics at TC = 25°C unless otherwise specified

Parameter	Symbol	Unit	Min	Typ	Max
Center Wavelength	λc	nm	1081	1083	1085
Optical Output Power @ LIV current	P <sub>o</sub>	mW	40-120		
Slope Efficiency, <u>1/</u>	ηd	W/A	0.3	0.36	
Slope Efficiency	ηd	W/A	0.6	0.72	-
Threshold Current	I <sub>th</sub>	mA	-	30	40
Laser Series Resistance	R <sub>s</sub>	Ω	-	2.0	2.5
Laser Forward Voltage	V <sub>f</sub>	V	-	2.0	2.5
Thermistor Resistance @25°C, <u>2/</u>	R <sub>T</sub>	KΩ	-	10	-
Photodiode Dark Current, V <sub>R</sub> =10V, LD I <sub>F</sub> =0, <u>2/</u>	I <sub>D</sub>	nA	-	-	50
Beam Divergence @ FWHM	θ X θ <sub>⊥</sub>	°	-	6 X 32	8 X 34
Laser Line Width	Δv	MHz	-	8	10
Side Mode Suppression Ratio	SMSR	dB	-30	-	-
Polarization Extinction Ratio, <u>1/</u>	PER	dB	-16	-19	-
Laser Polarization				TE	
Mode Structure				Fundamental Mode	

1/ Butterfly package 2/ TO-8 package

## Handling Precautions

These devices are sensitive to ESD. When handling the module, grounded work area and wrist strap must be used. Always store in an antistatic

container with all leads shorted together.

## Package

TO8	Butterfly
	